

**Amendments to the Claims**

1. (Cancelled)
2. (Cancelled)
3. (Cancelled)
4. (Cancelled)
5. (Cancelled)
6. (Cancelled)
7. (Cancelled)
8. (Currently Amended) A method of forming a trim fuse comprising the steps of:  
forming a stepped oxide region on a semiconductor substrate;  
forming at least one thinned oxide region on said semiconductor substrate and proximal said stepped oxide region wherein said at least one thinned oxide region is formed by diffusing a dopant into the semiconductor substrate and wherein the stepped oxide region is formed when an oxide layer is formed over the diffusion area on the substrate and non-diffusion areas on the substrate; and  
depositing an electrically blowable fuse material on said stepped oxide region and said at least one thinned oxide region to form at least one transition region such that said fuse material changes in thickness as it transitions between said at least one thinned oxide region and said stepped oxide region.

9. (Original) The method according to claim 8 wherein said step of depositing an electrically blowable fuse material on said stepped oxide region and said at least one thinned oxide region comprises forming said at least one transition region such that said fuse material reduces in thickness as it transitions from said at least one thinned oxide region to said stepped oxide region.
10. (Cancelled)
11. (Cancelled)
12. (Cancelled)
13. (Cancelled)
14. (Cancelled)
15. (Cancelled)
16. (Currently Amended) The method of forming a trim fuse according to Claim 8 wherein said fuse material comprises metal.
17. (Currently Amended) The method of forming a trim fuse according to Claim 9 wherein said fuse material comprises metal.
18. (Currently Amended) The method of forming a trim fuse according to Claim 16 wherein said metal comprises Al/Cu.
19. (Currently Amended) The method of forming a trim fuse according to Claim 17 wherein and metal comprises Al/Cu.
20. (Currently Amended) The method of forming a trim fuse according to Claim 8 wherein said fuse material comprises polycrystal silicon.
21. (Currently Amended) The method of forming a trim fuse according to Claim 9 wherein said fuse material comprises polycrystal silicon.
22. (Currently Amended) The method of forming a trim fuse according to Claim 8 wherein said semiconductor substrate comprises silicon.

23. (Currently Amended) The method of forming a trim fuse according to Claim 9 wherein said semiconductor substrate comprises silicon.
24. (New) The method of forming a trim fuse according to Claim 8 wherein a pair of diffusion areas are formed in the semiconductor substrate with a non-diffusion area therebetween and wherein the stepped oxide region is formed when an oxide layer is formed over the diffusion and non-diffusion areas.
25. (New) The method of Claim 8 wherein the diffusion step comprises thinning or removing an oxide layer formed on a semiconductor substrate, and diffusing a dopant into the semiconductor substrate.
26. (New) The method of Claim 24 wherein the diffusion step comprises thinning or removing an oxide layer formed on a semiconductor substrate, and diffusing a dopant into the semiconductor substrate.
27. (New) The method of Claim 8 wherein the diffusion area is not associated with the formation of a semiconductor device.
28. (New) The method of Claim 24 wherein the diffusion area is not associated with the formation of a semiconductor device.
29. (New) The method of Claim 25 wherein the diffusion area is not associated with the formation of a semiconductor device.
30. (New) The method of Claim 26 wherein the diffusion area is not associated with the formation of a semiconductor device.